

**NOT RECOMMENDED FOR NEW DESIGN**  
USE [DMP3036SSS](#)

## ZXM66P03N8

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### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

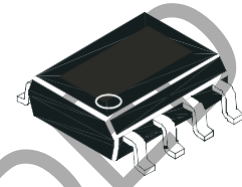
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#### SUMMARY

$V_{(BR)DSS} = -30V$ ;  $R_{DS(ON)} = 0.025\Omega$ ;  $I_D = -7.9A$

#### DESCRIPTION

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



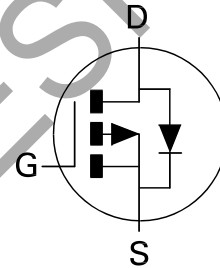
SO8

#### FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

#### APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control



#### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM66P03N8TA	7"	12mm	500 units
ZXM66P03N8TC	13"	12mm	2500 units



Top View

#### DEVICE MARKING

- ZXM  
66P03

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ISSUE 1 - JANUARY 2006

# ZXM66P03N8

## ABSOLUTE MAXIMUM

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate- Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $V_{GS}=-10V; T_A=25^{\circ}C(b)$ $V_{GS}=-10V; T_A=70^{\circ}C(b)$ $V_{GS}=-10V; T_A=25^{\circ}C(a)$	$I_D$	-7.9 -6.3 -6.25	A
Pulsed Drain Current (c)	$I_{DM}$	-28	A
Continuous Source Current (Body Diode)(b)	$I_S$	-4.1	A
Pulsed Source Current (Body Diode)(c)	$I_{SM}$	-28	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	$P_D$	1.56 12.5	W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	$P_D$	2.5 20	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	80	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	50	$^{\circ}C/W$

### NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions  
(b) For a device surface mounted on FR4 PCB measured at  $t_{\text{diamond}} 10$  secs.  
(c) Repetitive rating 25mm x 25mm FR4 PCB,  $D = 0.05$ , pulse width 101-s - pulse width limited by maximum junction temperature.

## ZXM66P03N8

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$			-1	$\mu\text{A}$	$V_{DS} = -24\text{V}$ , $V_{GS} = 0\text{V}$
Gate-Body Leakage	$I_{GSS}$			-100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.025 0.035	$\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -5.6\text{A}$ $V_{GS} = -4.5\text{V}$ , $I_D = -2.8\text{A}$
Forward Transconductance (1)(3)	$g_{fs}$		14.4		S	$V_{DS} = -15\text{V}$ , $I_D = -5.6\text{A}$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		1979		pF	$V_{DS} = -25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$		743		pF	
Reverse Transfer Capacitance	$C_{rss}$		279		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		7.6		ns	$V_{DD} = -15\text{V}$ , $I_D = -5.6\text{A}$ $R_G = 6.2\Omega$ , $V_{GS} = -10\text{V}$
Rise Time	$t_r$		16.3		ns	
Turn-Off Delay Time	$t_{d(off)}$		94.6		ns	
Fall Time	$t_f$		39.6		ns	
Gate Charge	$Q_g$		36		nC	$V_{DS} = -15\text{V}$ , $V_{GS} = -5\text{V}$ $I_D = -5.6\text{A}$
Total Gate Charge	$Q_g$		62.5		nC	$V_{DS} = -15\text{V}$ , $V_{GS} = -10\text{V}$ $I_D = -5.6\text{A}$
Gate-Source Charge	$Q_{gs}$		4.9		nC	
Gate Drain Charge	$Q_{gd}$		19.6		nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$			-0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = -5.6\text{A}$ , $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	$t_{rr}$		35		ns	$T_j = 25^{\circ}\text{C}$ , $I_F = -5.6\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	$Q_{rr}$		39.9		nC	

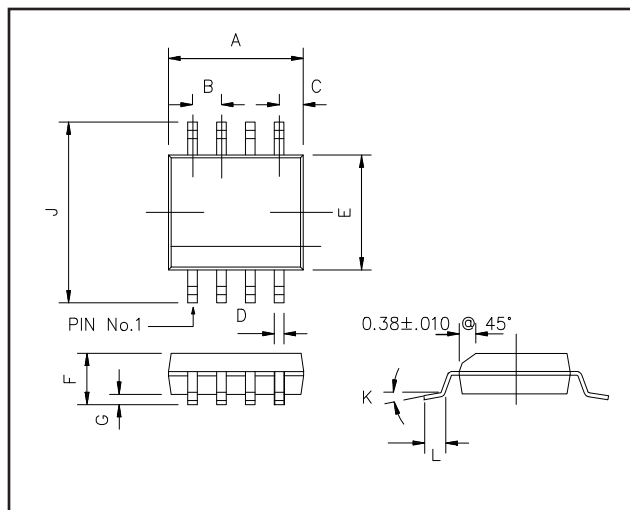
(1) Measured under pulsed conditions. Width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$  .

(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

# ZXM66P03N8

## PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	4.80	4.98	0.189	0.196
B	1.27 BSC		0.05 BSC	
C	0.53 REF		0.02 REF	
D	0.36	0.46	0.014	0.018
E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.05	0.07
G	0.10	0.25	0.004	0.010
J	5.80	6.20	0.23	0.24
K	0°	8°	0°	8°
L	0.41	1.27	0.016	0.050

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